



**Description**

The HSBB10P15 uses advanced trench MOSFET technology to provide excellent  $R_{DS(ON)}$  and gate charge for use in a wide variety of other applications.

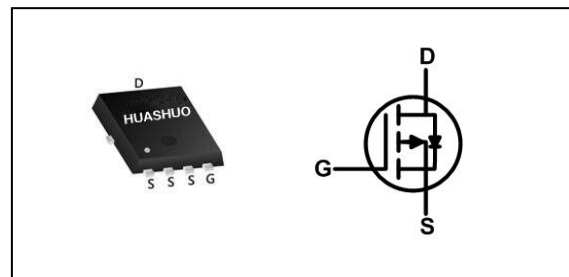
The HSBB10P15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

**Product Summary**

$V_{DS}$	-150	V
$R_{DS(ON),typ}$	290	m $\Omega$
$I_D$	-10	A

**PRPAK3\*3 Pin Configuration**



**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-150	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-10	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-7	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-35	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	73	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	35	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	2.9	$^\circ C/W$



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-150	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A	---	290	345	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-2	-2.7	-4	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-150V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ± 20V, V <sub>DS</sub> =0V	---	---	± 100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-5A	---	10	---	S
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1.0MHz	---	5	---	Ω
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A	---	39	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	8.1	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	9.5	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-50V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-5A	---	33	---	ns
T <sub>r</sub>	Rise Time		---	27	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	250	---	
T <sub>f</sub>	Fall Time		---	130	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V, f=1MHz	---	2021	---	pF
C <sub>oss</sub>	Output Capacitance		---	44	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	37	---	

**Diode Characteristics**

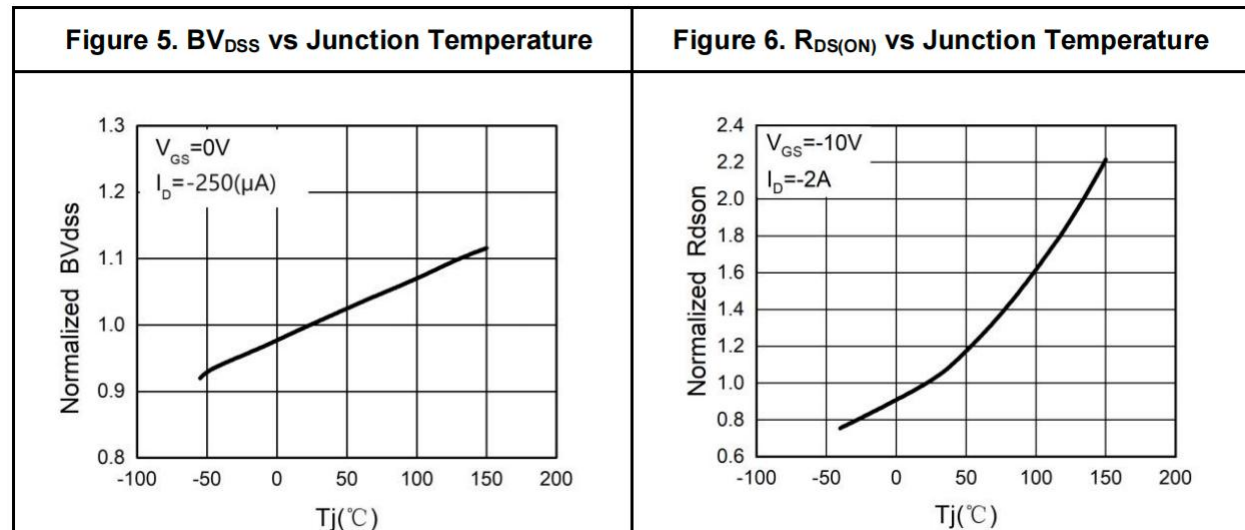
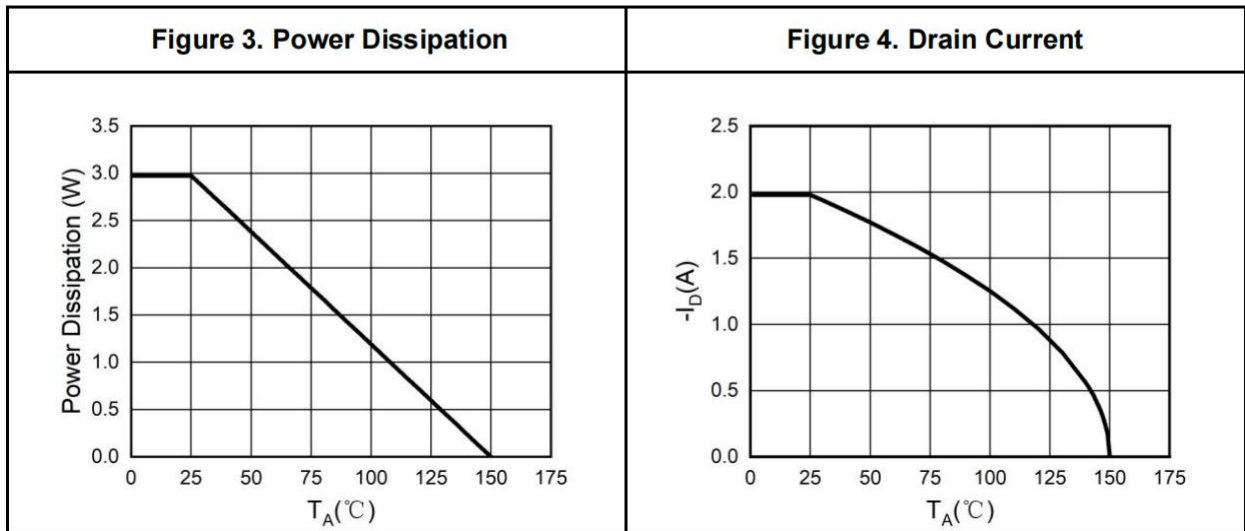
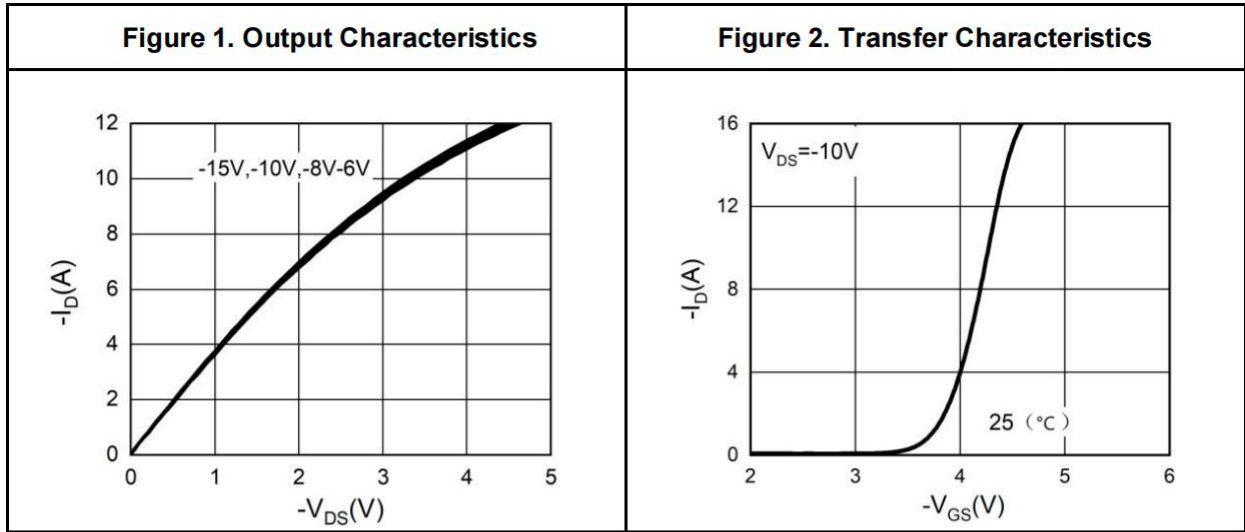
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-10	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-2A, di/dt=-100A/μs, T <sub>J</sub> =25°C	---	35	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	32	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=-50V,V<sub>GS</sub>=-10V,L=0.5mH
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

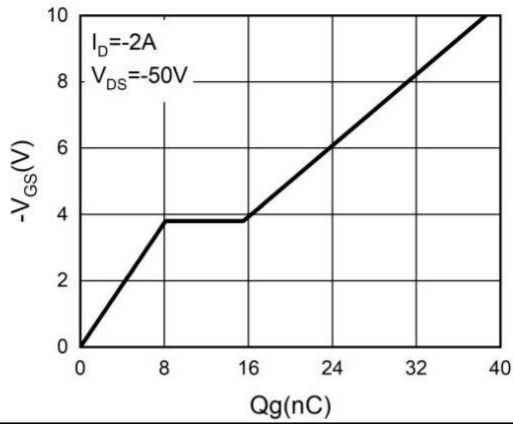


### Typical Characteristics

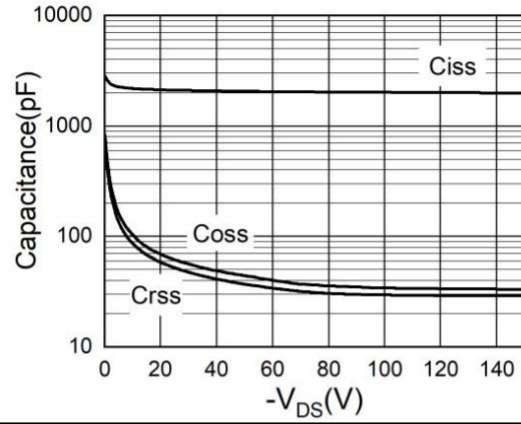




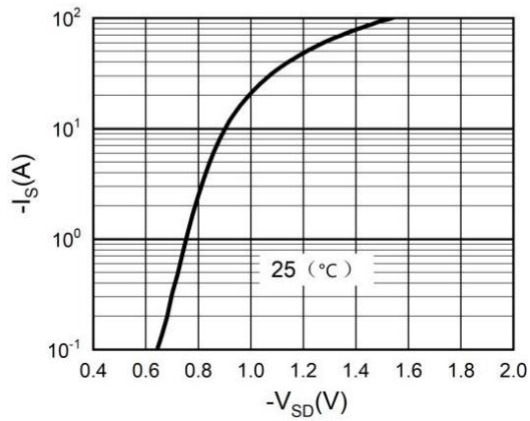
**Figure 7. Gate Charge Waveforms**



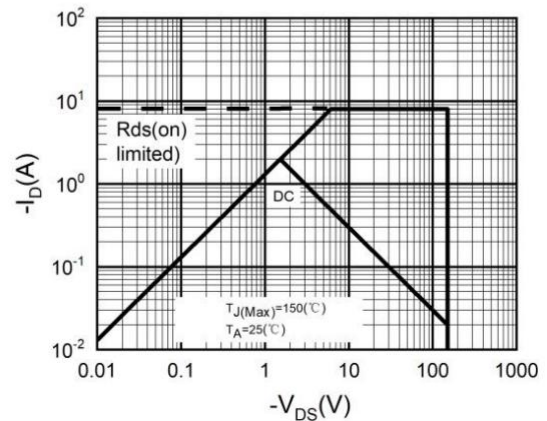
**Figure 8. Capacitance**



**Figure 9. Body-Diode Characteristics**



**Figure 10. Maximum Safe Operating Area**

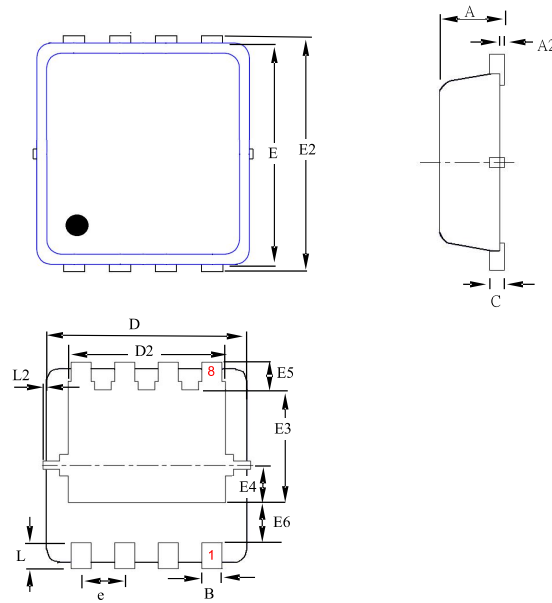




## Ordering Information

Part Number	Package code	Packaging
HSBB10P15	PRPAK3*3	3000/Tape&Reel

**PRPAK 3\*3(E) Single Outline**



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.028	0.031	0.035
A2	0.00	--	0.05	0.000	--	0.002
B	0.24	0.30	0.35	0.009	0.012	0.014
C	0.10	0.15	0.25	0.004	0.006	0.010
D	2.90	3.00	3.20	0.114	0.118	0.126
D2	2.15	2.35	2.59	0.085	0.093	0.102
E	2.90	3.00	3.12	0.114	0.118	0.123
E2	3.05	3.20	3.45	0.120	0.126	0.136
E3	1.55	1.75	1.95	0.061	0.069	0.077
E4	0.48	0.58	0.68	0.019	0.023	0.027
E5	0.28	0.43	0.58	0.011	0.017	0.023
E6	0.43	0.63	0.87	0.017	0.025	0.034
L	0.30	0.40	0.50	0.012	0.016	0.020
L2	0.00	--	0.10	0.000	--	0.004
e	--	0.65	--	--	0.026	--

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